

Features

- Low on resistance
- Low reverse transfer capacitances
- 100% single pulse avalanche energy test
- 100% ΔVDS test
- Pb-Free plating / Halogen-Free / RoHS compliant

Applications

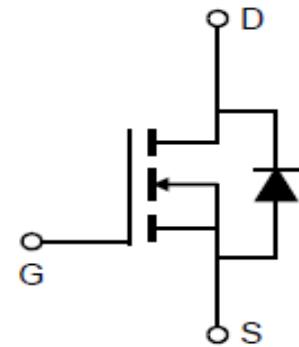
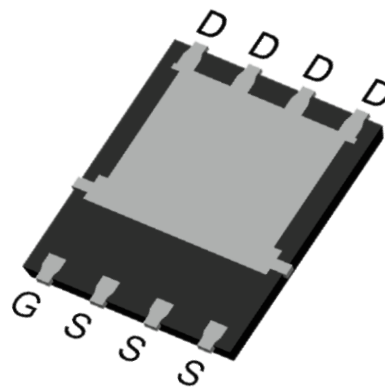
- Power switching applications
- DC-DC converters
- Full bridge control

Key Parameters

V_{DS}	80V
$R_{DS(on)typ.}$	3.4mΩ
V_{TH}	3V
$I_{D(Silicon\ limit)}$	133A
$I_{D(Package\ limit)}$	100A
$C_{iss@10V}$	3402pF
Q_{gd}	21nC



DFN5*6-8



Marking & Packing Information

Part #	Package	Marking	Tube/Reel	Qty(pcs)
DSP037N08N3	DFN5*6-8	DSP037N08N3	Tape&Reel	3000/box

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DS}	80	V
Gate-Source voltage	V_{GS}	±20	V
Continuous drain current $T_C = 25^\circ\text{C}$ (Silicon limit) $T_C = 25^\circ\text{C}$ (Package limit) $T_C = 100^\circ\text{C}$	I_D	133 100 84	A
Pulsed drain current ($T_C = 25^\circ\text{C}$, t_p limited by T_{jmax})	$I_{D\ pulse}$	533	A
Avalanche energy, single pulse ($L=0.5\text{mH}$, $R_g=25\Omega$)	E_{AS}	600	mJ
Power dissipation ($T_C = 25^\circ\text{C}$)	P_{tot}	125	W
Operating junction and storage temperature	T_j, T_{stg}	-55...+150	°C

Thermal Resistance

Parameter	Symbol	Max	Unit
Thermal resistance, junction – case.	R_{thJC}	1.0	°C/W

Electrical Characteristic (at $T_j = 25^\circ\text{C}$, unless otherwise specified)

Static Characteristic

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Drain-source breakdown voltage	BV_{DSS}	80	-	-	V	$V_{GS}=0V, I_D=250\mu A$
Gate threshold voltage	$V_{GS(th)}$	2.0	3.0	4.0	V	$V_{DS}=V_{GS}, I_D=250\mu A$
Zero gate voltage drain current	I_{DSS}	-	-	1 100	μA	$V_{DS}=80V, V_{GS}=0V$ $T_j=25^\circ\text{C}$ $T_j=125^\circ\text{C}$
Gate-source leakage current	I_{GSS}	-	-	100	nA	$V_{GS}=20V, V_{DS}=0V$
Drain-source on-state resistance	$R_{DS(on)}$	-	3.4	3.9	mΩ	$V_{GS}=10V, I_D=70A,$ $T_j=25^\circ\text{C}$
Transconductance	g_{fs}	-	130	-	S	$V_{DS}=5V, I_D=60A$

Dynamic Characteristic

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Input Capacitance	C_{iss}	-	3402	-	pF	$V_{GS}=0V, V_{DS}=40V,$ $f=1MHz$
Output Capacitance	C_{oss}	-	735	-		
Reverse Transfer Capacitance	C_{rss}	-	38	-		
Gate Total Charge	Q_G	-	64	-	nC	$V_{GS}=10V, V_{DS}=40V,$ $I_D=60A, f=1MHz$
Gate-Source charge	Q_{gs}	-	18	-		
Gate-Drain charge	Q_{gd}	-	21	-		
Gate plateau voltage	$V_{plateau}$	-	5.3	-	V	
Turn-on delay time	$t_{d(on)}$	-	16	-	ns	$V_{GS}=10V, V_{DD}=30V,$ $I_D=60A, R_{G_ext}=4.7\Omega$
Rise time	t_r	-	29	-		
Turn-off delay time	$t_{d(off)}$	-	42	-		
Fall time	t_f	-	30	-		
Gate resistance	R_G	-	2.8	-	Ω	$V_{GS}=0V, V_{DS}=0V,$ $f=1MHz$

Body Diode Characteristic

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Diode Max Current	I_S		-	100	A	-
Diode Forward Voltage	V_{SD}	-	-	1.2	V	$V_{GS}=0V, I_{SD}=60A$
Diode Reverse Recovery Time	t_{rr}	-	53	-	ns	$I_F=50A,$ $dI/dt=100A/\mu s$
Diode Reverse Recovery Charge	Q_{rr}	-	72	-	nC	

Typical Characteristics Diagram

Fig1. Output Characteristics

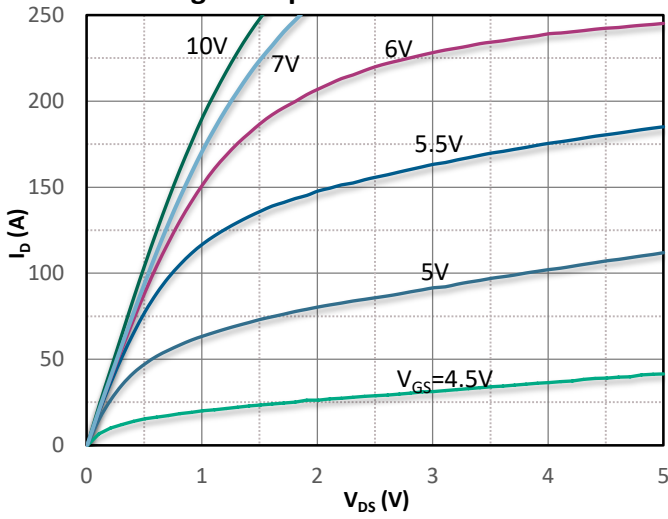


Fig2. Transfer Characteristics

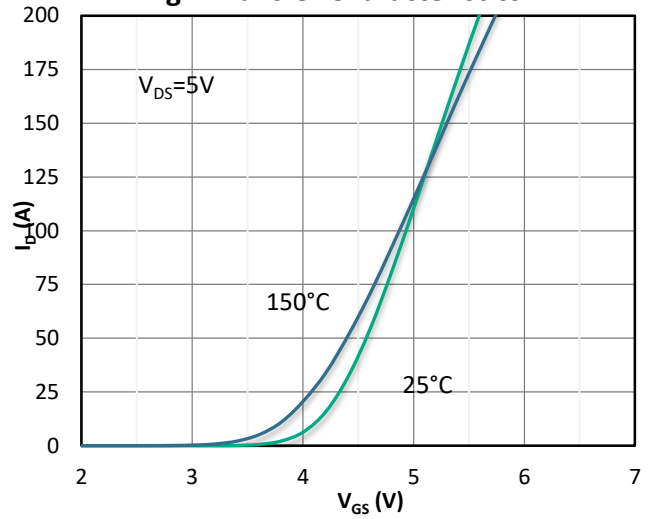


Fig3. Rds(on) vs Drain Current

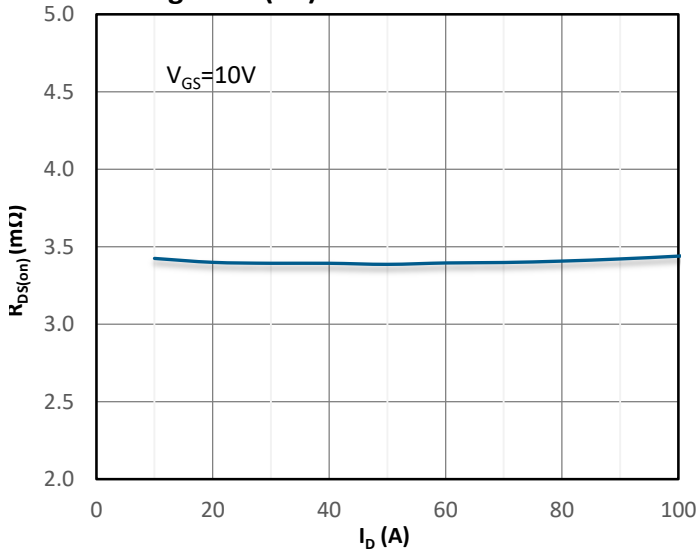


Fig 4. Rds(on) vs Gate Voltage

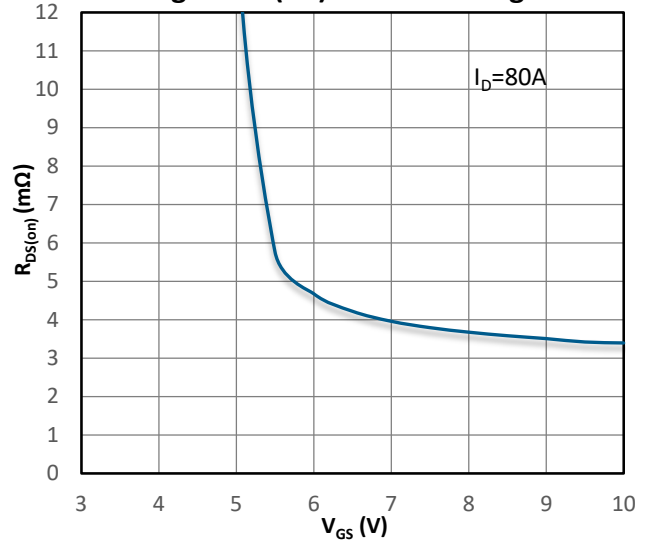


Fig5. Rds(on) vs. Temperature

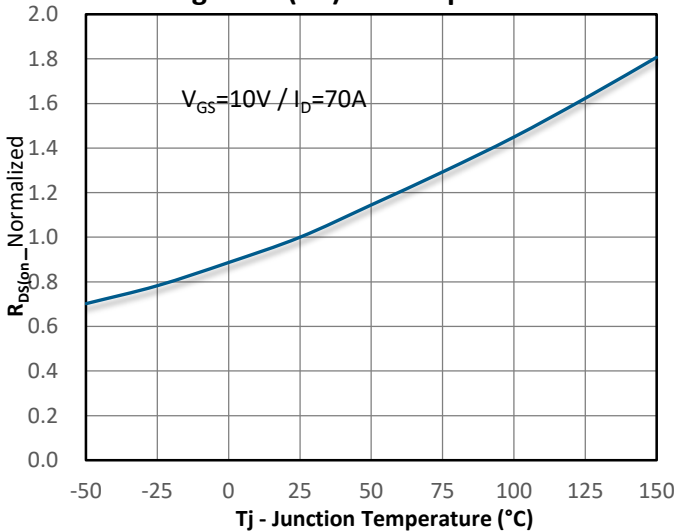
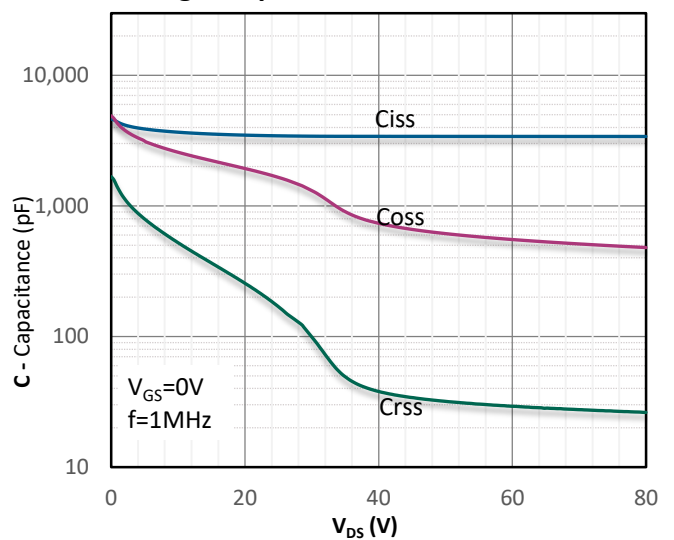
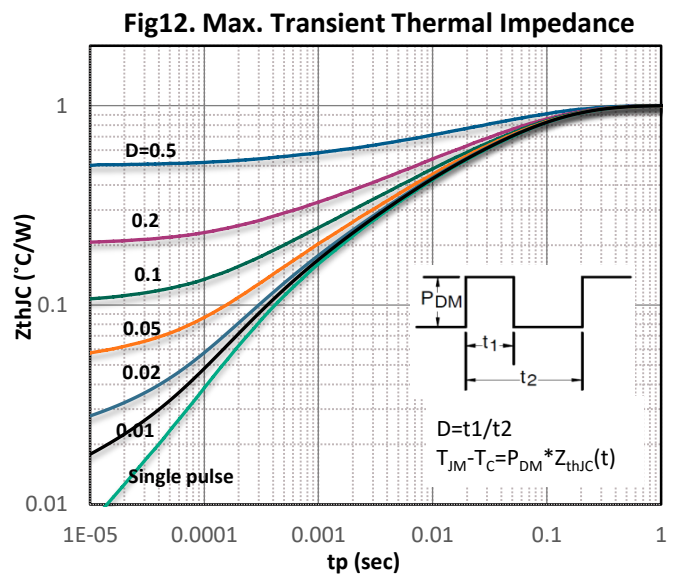
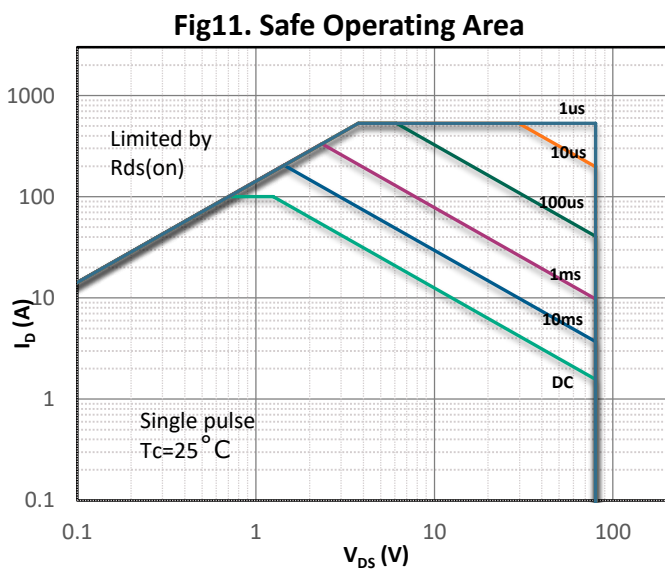
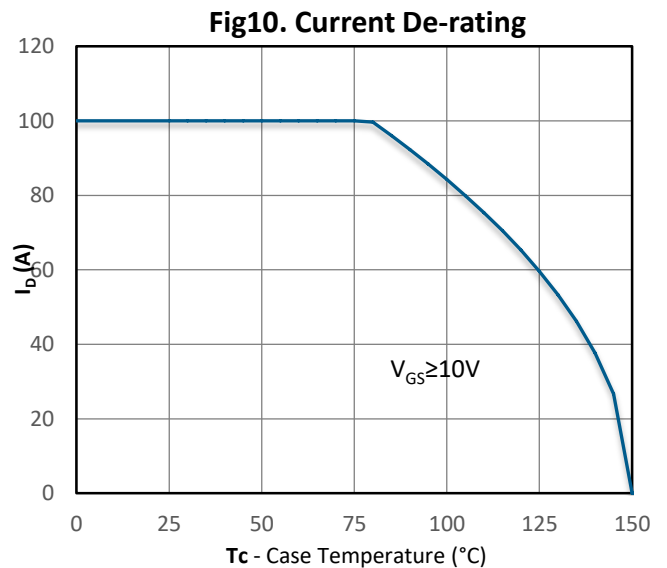
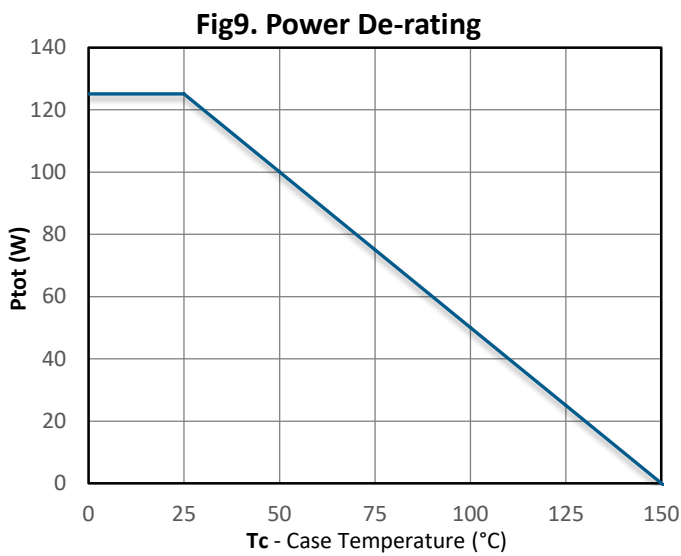
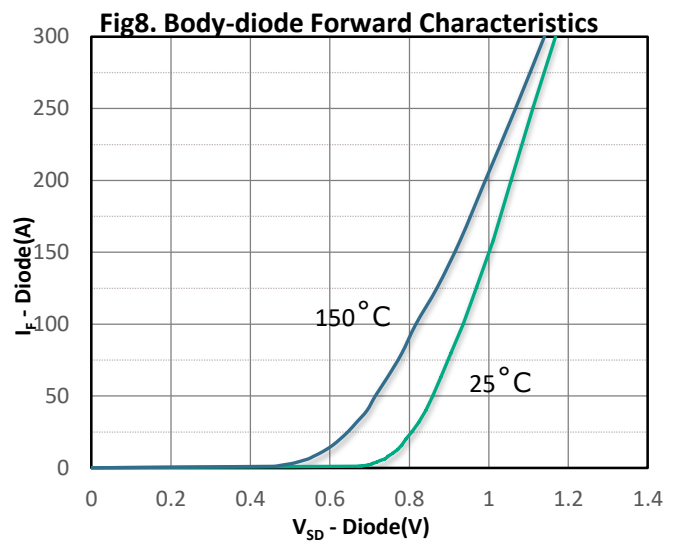
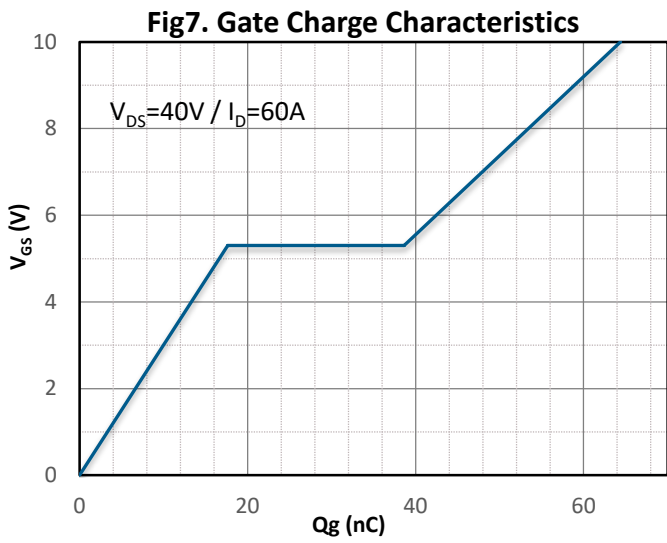


Fig6. Capacitance Characteristics

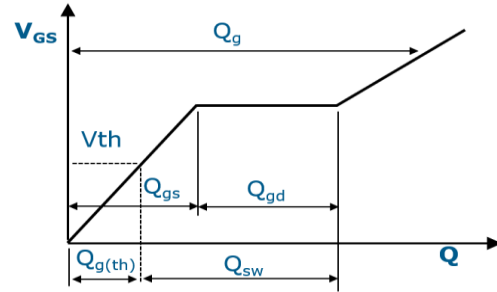
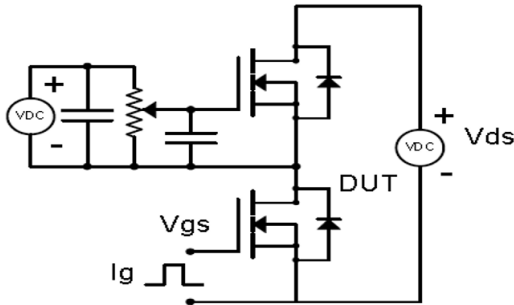


Typical Characteristics Diagram

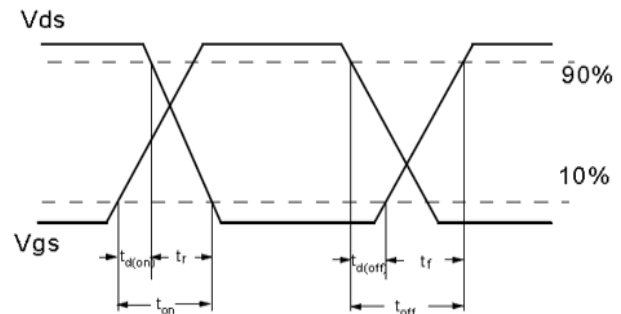
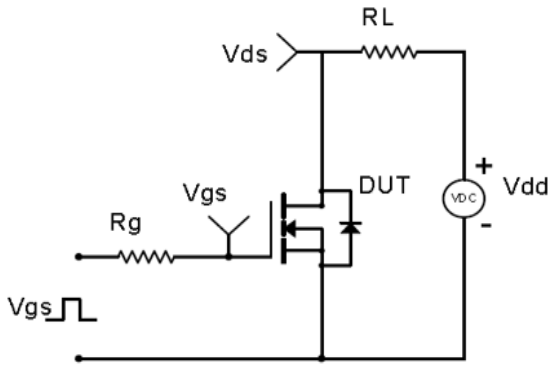


Test Circuit & Waveform

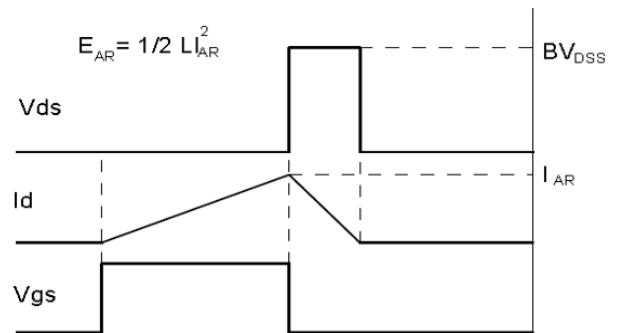
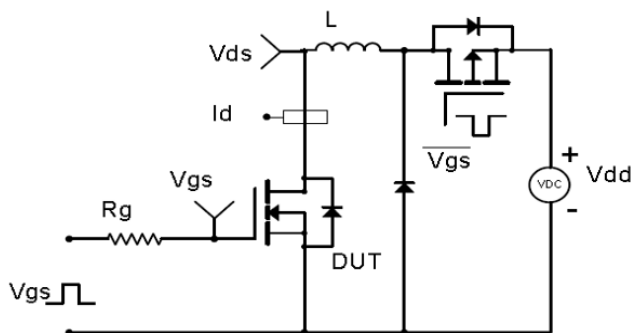
Gate Charge Test Circuit & Waveform



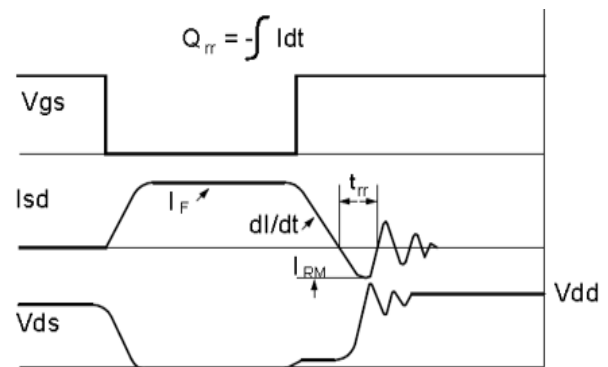
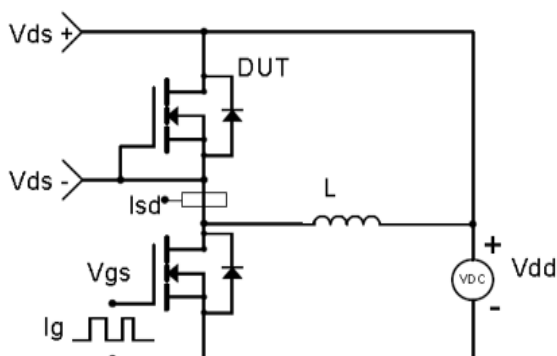
MOSFET Switching Test Circuit & Waveform



E_{AS} Test Circuit & Waveform

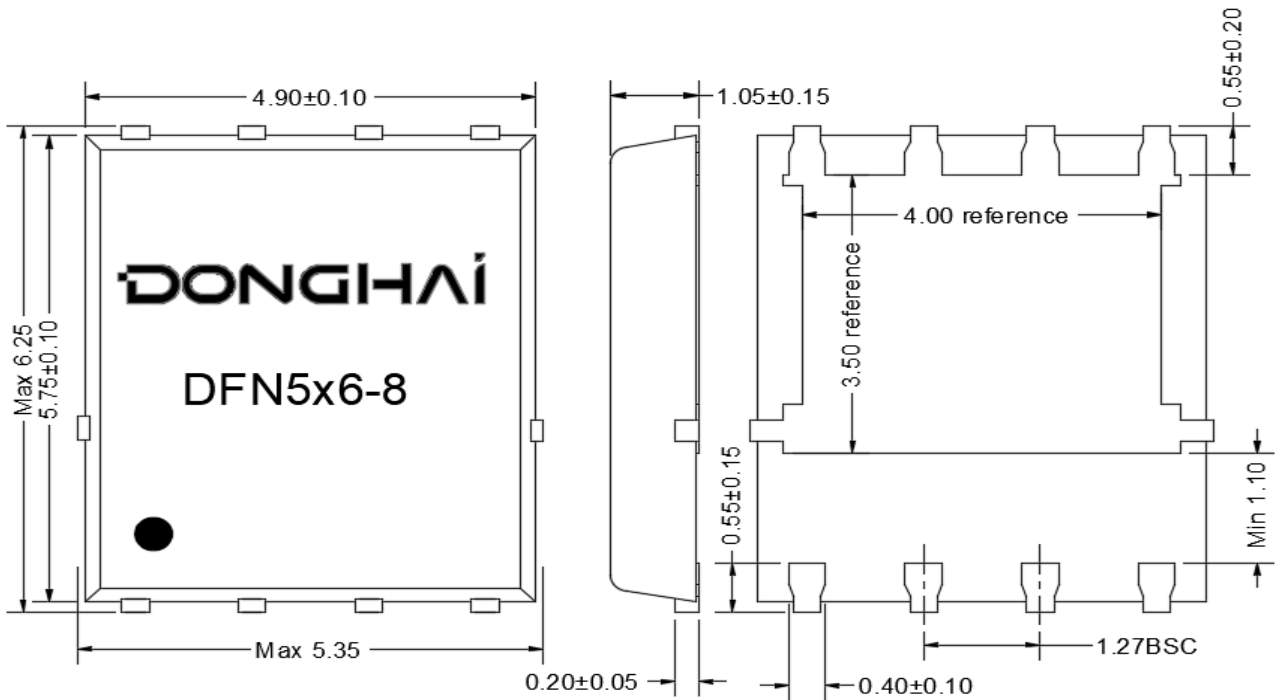


Diode Recovery Test Circuit & Waveform



Package Outline : DFN5*6

*Dimensions in mm



Revision History

Revision	Date	Major changes
1.0	2023/8/23	Release of formal version

Disclaimer

Unless otherwise specified in the datasheet, the product is designed and qualified as a standard commercial product and is not intended for use in applications that require extraordinary levels of quality and reliability, such as aviation, aerospace, life-support devices or systems.

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